RELIABILITY REPORT
FOR
MAX2644EXT+
PLASTIC ENCAPSULATED DEVICES

December 17, 2008

MAXIM INTEGRATED PRODUCTS
120 SAN GABRIEL DR.
SUNNYVALE, CA 94086

<table>
<thead>
<tr>
<th>Approved by</th>
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<tbody>
<tr>
<td>Ken Wendel</td>
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<tr>
<td>Quality Assurance</td>
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<tr>
<td>Director, Reliability Engineering</td>
</tr>
</tbody>
</table>
Conclusion

The MAX2644EXT+ successfully meets the quality and reliability standards required of all Maxim products. In addition, Maxim's continuous reliability monitoring program ensures that all outgoing product will continue to meet Maxim's quality and reliability standards.

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I. Device Description

A. General

The MAX2644 low-cost, high third-order intercept point (IP3) low-noise amplifier (LNA) is designed for applications in 2.4GHz WLAN, ISM, and Bluetooth® radio systems. It features a programmable bias, allowing the input IP3 and supply current to be optimized for specific applications. The LNA provides up to +1dBm input IP3 while maintaining a low noise figure of 2.0dB and a typical gain of 16dB. The MAX2644 is designed on a low-noise, advanced silicon-germanium (SiGe) technology. It operates with a +2.7V to +5.5V single supply and is available in an ultra-small 6-pin SC70 package.
II. Manufacturing Information

A. Description/Function: 2.4GHz SiGe, High IP3 Low-Noise Amplifier
B. Process: GST3
C. Number of Device Transistors: 
D. Fabrication Location: Oregon
E. Assembly Location: Carsem Malaysia, UTL Thailand
F. Date of Initial Production: July 22, 2000

III. Packaging Information

A. Package Type: 6-pin SC70
B. Lead Frame: Cu Alloy
C. Lead Finish: 100% matte Tin
D. Die Attach: Non Conductive Epoxy
E. Bondwire: Au (1.0 mil dia.)
F. Mold Material: Epoxy with silica filler
G. Assembly Diagram: 
H. Flammability Rating: Class UL94-V0
I. Classification of Moisture Sensitivity per JEDEC standard J-STD-020-C
J. Single Layer Theta Ja: 326°C/W
K. Single Layer Theta Jc: 115°C/W

IV. Die Information

A. Dimensions: 30 X 29 mils
B. Passivation: Si$_3$N$_4$ (Silicon nitride)
C. Interconnect: Gold
D. Backside Metallization: None
E. Minimum Metal Width: Metal1 = 0.5 / Metal2 = 0.6 / Metal3 = 0.6 microns (as drawn)
F. Minimum Metal Spacing: Metal1 = 0.45 / Metal2 = 0.5 / Metal3 = 0.6 microns (as drawn)
G. Bondpad Dimensions: 5 mil. Sq.
H. Isolation Dielectric: SiO$_2$
I. Die Separation Method: Wafer Saw
V. Quality Assurance Information

A. Quality Assurance Contacts: Ken Wendel (Director, Reliability Engineering)  
   Bryan Preeshl (Managing Director of QA)

B. Outgoing Inspection Level: 0.1% for all electrical parameters guaranteed by the Datasheet.  
   0.1% For all Visual Defects.

C. Observed Outgoing Defect Rate: < 50 ppm

D. Sampling Plan: Mil-Std-105D

VI. Reliability Evaluation

A. Accelerated Life Test

   The results of the 150°C biased (static) life test are in Table 1. Using these results, the Failure Rate (λ) is calculated as follows:

\[
\lambda = \frac{1}{\text{MTTF}} = \frac{1.83}{192 \times 4340 \times 43 \times 2}
\]

(Chi square value for MTTF upper limit)

\[
(\text{where } 4340 = \text{Temperature Acceleration factor assuming an activation energy of } 0.8eV)
\]

\[
\lambda = \frac{11.1 \times 10^{-9}}{11.1 \times 10^{-9}} = 1.1 \text{ F.I.T. (60% confidence level @ 25°C)}
\]

The following failure rate represents data collected from Maxim’s reliability monitor program. Maxim performs quarterly 1000 hour life test monitors on its processes. This data is published in the Product Reliability Report found at http://www.maxim-ic.com/. Current monitor data for the GST3 Process results in a FIT Rate of 0.21 @ 25C and 3.64 @ 55C (0.8 eV, 60% UCL)

B. Moisture Resistance Tests

   The industry standard 85°C/85%RH or HAST testing is monitored per device process once a quarter.

C. E.S.D. and Latch-Up Testing

   The WR70-1 die type has been found to have all pins able to withstand a HBM transient pulse of +/-2000 V per Mil-Std 883 Method 3015.7. Latch-Up testing has shown that this device withstands a current of +/-250 mA.
### Table 1
Reliability Evaluation Test Results

<table>
<thead>
<tr>
<th>TEST ITEM</th>
<th>TEST CONDITION</th>
<th>FAILURE IDENTIFICATION</th>
<th>SAMPLE SIZE</th>
<th>NUMBER OF FAILURES</th>
</tr>
</thead>
<tbody>
<tr>
<td><strong>Static Life Test</strong> (Note 1)</td>
<td>Ta = 150°C Biased Time = 192 hrs.</td>
<td>DC Parameters &amp; functionality</td>
<td>43</td>
<td>0</td>
</tr>
<tr>
<td><strong>Moisture Testing</strong> (Note 2)</td>
<td>Ta = 85°C RH = 85% Biased Time = 1000hrs.</td>
<td>DC Parameters &amp; functionality</td>
<td>77</td>
<td>0</td>
</tr>
<tr>
<td><strong>Mechanical Stress</strong> (Note 2)</td>
<td>Temperature Cycle</td>
<td>DC Parameters &amp; functionality</td>
<td>77</td>
<td>0</td>
</tr>
<tr>
<td></td>
<td>-65°C/150°C 1000 Cycles Method 1010</td>
<td></td>
<td></td>
<td></td>
</tr>
</tbody>
</table>

Note 1: Life Test Data may represent plastic DIP qualification lots.
Note 2: Generic Package/Process data